

ISD1447AS1**PRELIMINARY**

Notice: This is not a final specification Some parametric are subject to change.

FOR LOW FREQUENCY POWOR AMPLIFY APPLICATION
SILICON NPN EPITAXIAL TYPE

DESCRIPTION

ISD1447AS1 is a silicon NPN epitaxial type transistor designed for 2 to 3.5W output low frequency power amplify application. Complementary with ISB1035AS1.

FEATURE

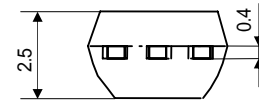
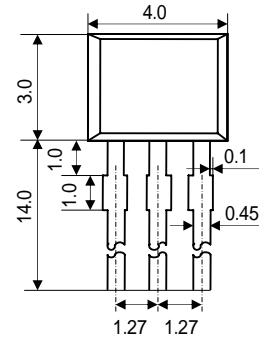
High collector current. $I_{CM}= 1.5A$
High gain band width product. $f_T= 100MHz$ typ
High collecot dissipation. $P_c= 600mW$
Excellent linearity of DC forward current gain.

APPLICATION

2 to 3.5W output low frequency amplify circuit of radio, cassette tape recorder, mini stereo.

OUTLINE DRAWING

Unit: mm



JEITA:
JEDEC:

TERMINAL CONNECTER

: EMITTER
: COLLECTOR
: BASE

MAXIMUM RATINGS ($T_a=25$)

Symbol	Parameter	Ratings	Unit
V_{CBO}	Collector to Base voltage	30	V
V_{EBO}	Emitter to Base voltage	4	V
V_{CEO}	Collector to Emitter voltage	25	V
I_C	Collector current	1	A
I_{CM}	Peak collector current	1.5	A
P_c	Collector dissipation	600	mW
T_j	Junction temperature	+150	
T_{stg}	Storage temperature	-55 ~ +150	

ELECTRICAL CHARACTERISTICS ($T_a=25$)

Parameter	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
$V_{(BR)CBO}$	C to B break down voltage	$I_C= 10 \mu A, I_E=0mA$	30	-	-	V
$V_{(BR)EBO}$	E to B break down voltage	$I_E= 10 \mu A, I_C=0mA$	4	-	-	V
$V_{(BR)CEO}$	C to E break down voltage	$I_C= 100 \mu A, R_{BE}=\infty$	25	-	-	V
I_{CBO}	Collector cut off current	$V_{CB}= 25V, I_E= 0mA$	-	-	1	μA
I_{EBO}	Emitter cut off current	$V_{EB}=2V, I_C= 0mA$	-	-	1	μA
hFE	DC forward current gain	$V_{CE}= 1V, I_C= 500mA$	55	-	300	-
$V_{CE(sat)}$	C to E Saturation Voltage	$I_C=500mA, I_B= 25mA$	-	-	0.5	V
f_T	Gain band width product	$V_{CE}=6V, I_E= -10mA$	-	100	-	MHz

) It shows hFE classification in right table.

Item	D	E	F
hFE item	55 ~ 110	90 ~ 180	150 ~ 300

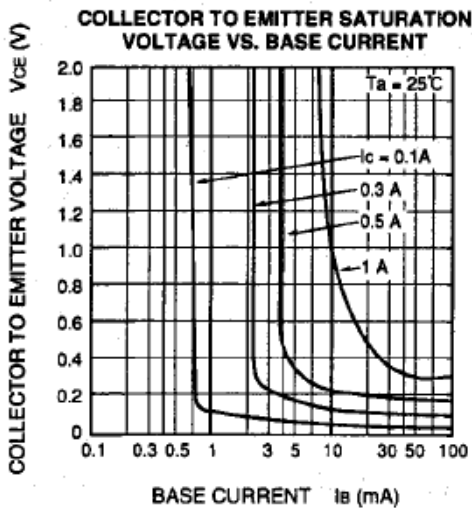
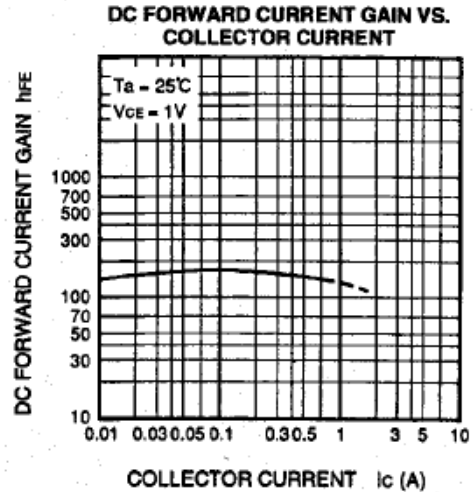
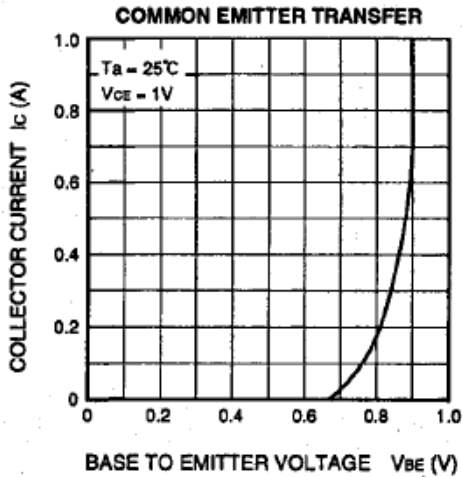
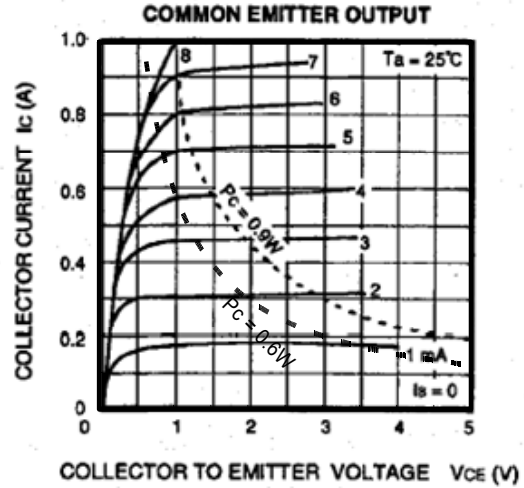
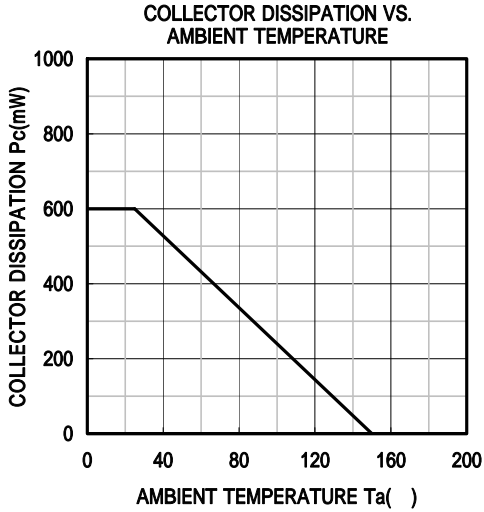
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TYPICAL CHARACTERISTICS





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